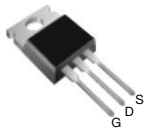
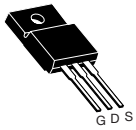
# Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) at $T_J$ max. | 560 V | |
| $R_{DS(on)}$ (Ω) | $V_{GS}$ = 10 V | 0.38 |
| $Q_g$ (Max.) (nC) | 68 | |
| $Q_{gs}$ (nC) | 17.6 | |
| $Q_{gd}$ (nC) | 21.8 | |
| Configuration | Single | |

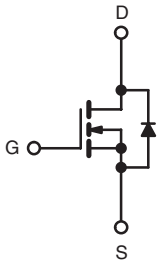
TO-220AB




TO-220 FULLPAK




D²PAK (TO-263)


N-Channel MOSFET

## FEATURES

- Low Figure-of-Merit $R_{on}$ x $Q_g$
- 100 % Avalanche Tested
- Gate Charge Improved
- $T_{rr}/Q_{rr}$ Improved
- Compliant to RoHS Directive 2002/95/EC

Available
RoHS* COMPLIANT

| ORDERING INFORMATION | | | |
|---|---|---|---|
| Package | TO-220AB | D²PAK (TO-263) | TO-220 FULLPAK |
| Lead (Pb)-free | SiHP16N50C-E3 | SiHB16N50C-E3 | SiHF16N50C-E3 |

**ABSOLUTE MAXIMUM RATINGS** $T_C$ = 25 °C, unless otherwise noted

| PARAMETER | | | SYMBOL | LIMIT TO220-AB D²PAK (TO-263) | LIMIT TO-220 FULLPAK | UNIT |
|---|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DS}$ | 500 | | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 30 | | |
| Continuous Drain Current ($T_J$ = 150 °C)[a] | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 16 | | A |
| | | $T_C$ = 100 °C | | 10 | | |
| Pulsed Drain Current[c] | | | $I_{DM}$ | 40 | | |
| Linear Derating Factor | | | | 2 | | W/°C |
| Single Pulse Avalanche Energy[b] | | | $E_{AS}$ | 320 | | mJ |
| Maximum Power Dissipation | | | $P_D$ | 250 | 38 | W |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | - 55 to + 150 | | °C |
| Soldering Recommendations (Peak Temperature)[d] | for 10 s | | | 300 | | |

**Notes**

a. Limited by maximum junction temperature.
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 2.5 mH, $R_g$ = 25 Ω, $I_{AS}$ = 16 A.
c. Repetitive rating; pulse width limited by maximum junction temperature.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TO220-AB D²PAK (TO-263)** | **TO-220 FULLPAK** | **UNIT** |
| Maximum Junction-to-Ambient | $R_{thJA}$ | 62 | 65 | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | 0.5 | 3.3 | |
| Junction-to-Ambient (PCB mount)[a] | $R_{thJA}$ | 40 | - | |

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

| SPECIFICATIONS $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 500 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 1 mA | - | 0.6 | - | V/°C |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 3.0 | - | 5.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 30 V | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 500 V, $V_{GS}$ = 0 V | - | - | 50 | µA |
| | | $V_{DS}$ = 400 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V; $I_D$ = 8 A | - | 0.31 | 0.38 | Ω |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 50 V, $I_D$ = 3 A | - | 3 | - | S |
| **Dynamic** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1.0 MHz | - | 1900 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 230 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 24 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V; $I_D$ = 16 A, $V_{DS}$ = 400 V | - | 45 | 68 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 18 | - | |
| Gate-Drain Charge | $Q_{gd}$ | | - | 22 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 250 V, $I_D$ = 16 A, $R_g$ = 9.1 Ω, $V_{GS}$ = 10 V | - | 27 | - | ns |
| Rise Time | $t_r$ | | - | 156 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 29 | - | |
| Fall Time | $t_f$ | | - | 31 | - | |
| Gate Input Resistance | $R_g$ | f = 1 MHz, open drain | - | 1.6 | - | Ω |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 16 | A |
| Pulsed Diode Forward Current | $I_{SM}$ | | - | - | 30 | |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 10 A, $V_{GS}$ = 0 V | - | - | 1.8 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = $I_S$, dI/dt = 100 A/µs, $V_R$ = 20 V | - | 555 | - | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | - | 5.5 | - | µC |
| Body Diode Reverse Recovery Current | $I_{RRM}$ | | - | 18 | - | A |

**Note**

- The information shown here is a preliminary product proposal, not a commercial product data sheet. Vishay Siliconix is not committed to produce this or any similar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

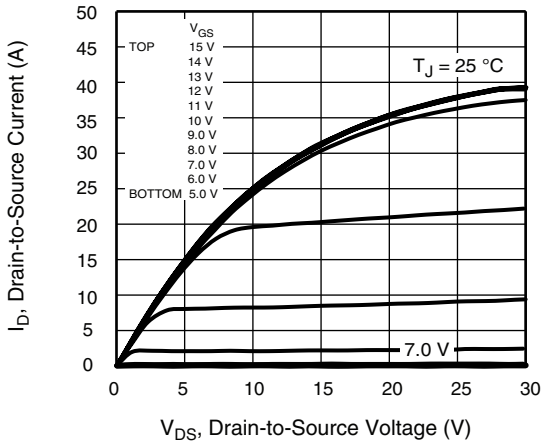



**Fig. 1 - Typical Output Characteristics (TO-220)**

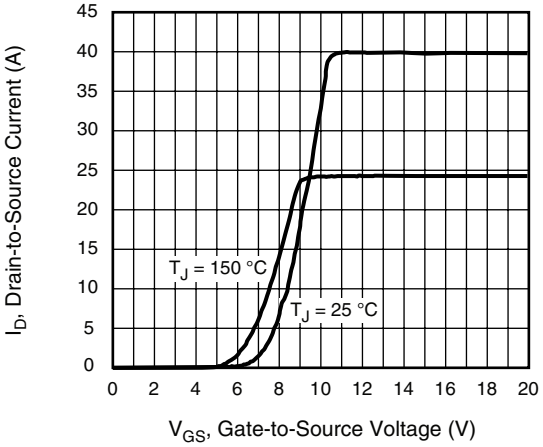



**Fig. 3 - Typical Transfer Characteristics**

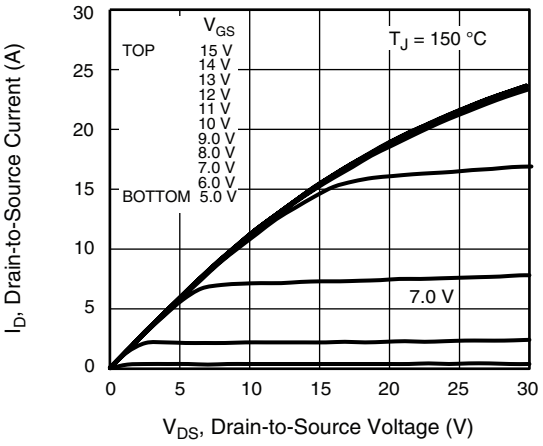



**Fig. 2 - Typical Output Characteristics (TO-220)**

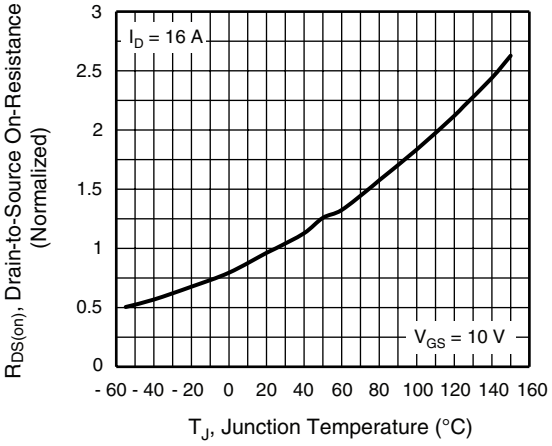



**Fig. 4 - Normalized On-Resistance vs. Temperature**

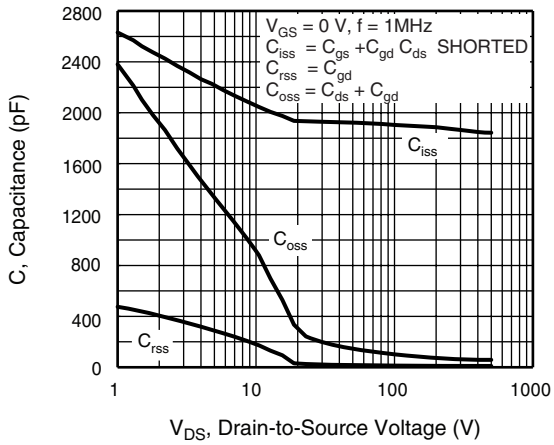



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

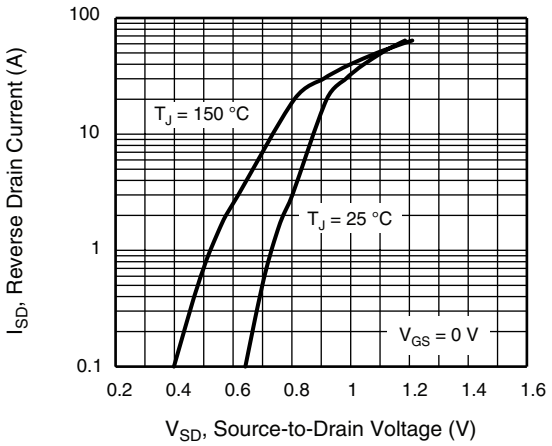



**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

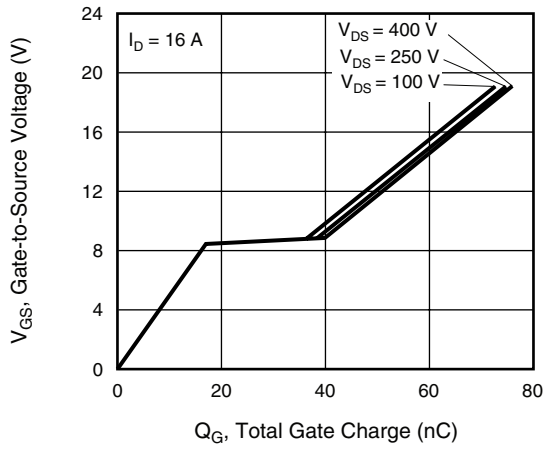



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

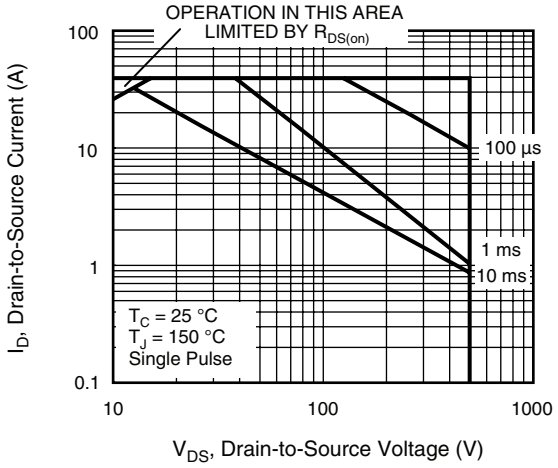



**Fig. 8 - Maximum Safe Operating Area (TO-220AB, $D^2PAK$)**

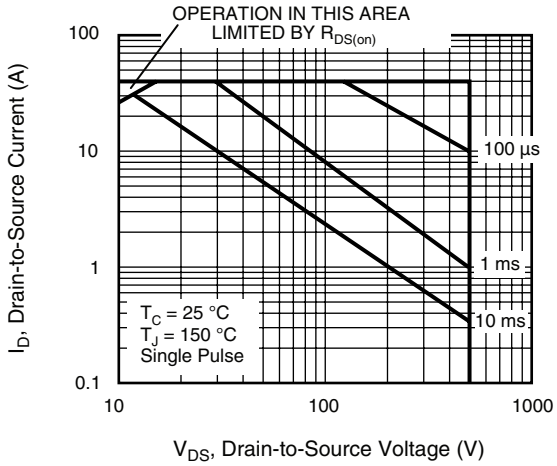



**Fig. 9 - Maximum Safe Operating Area (TO-220 FULLPAK)**

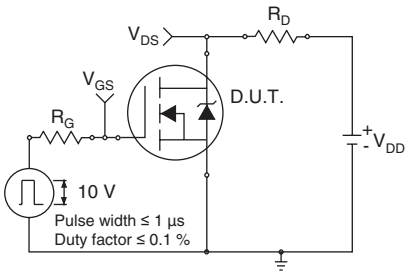



**Fig. 10a - Switching Time Test Circuit**

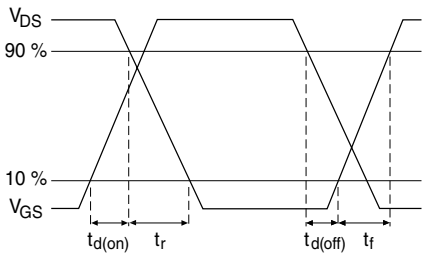



**Fig. 10b - Switching Time Waveforms**

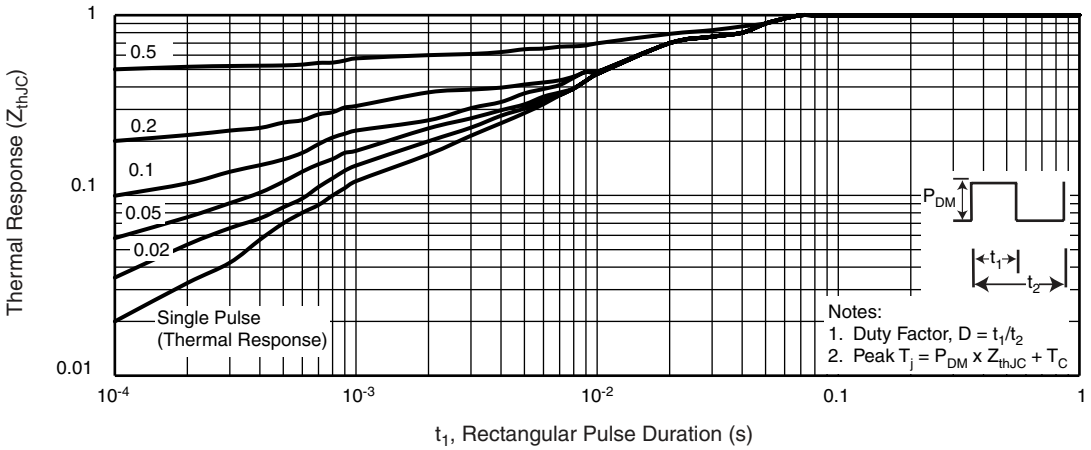



**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220AB, $D^2PAK$)**

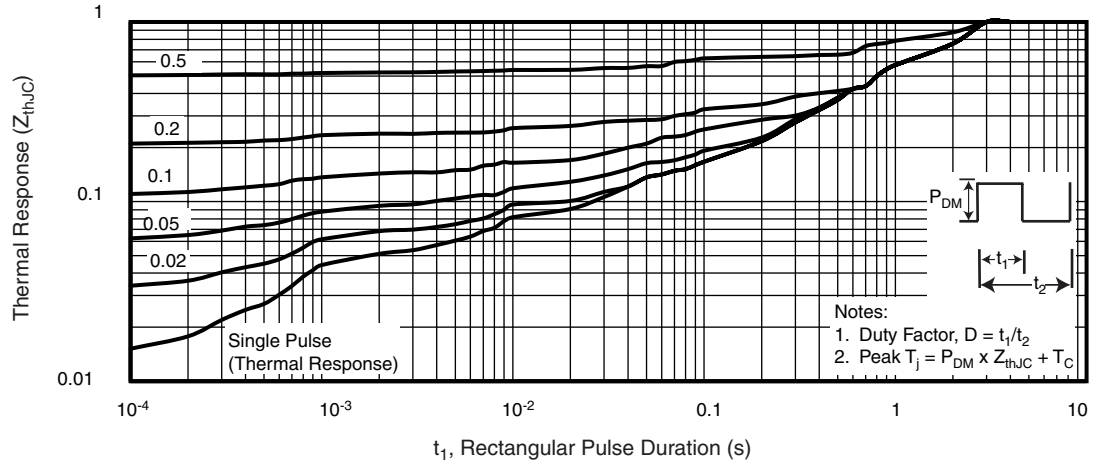



**Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220 FULLPAK)**

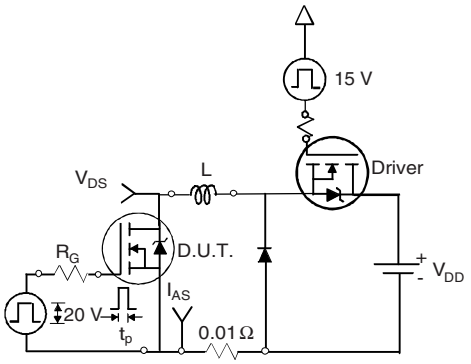



**Fig. 13a - Unclamped Inductive Test Circuit**

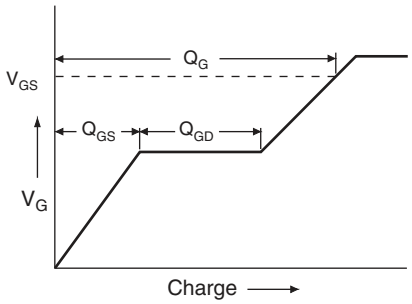



**Fig. 14a - Basic Gate Charge Waveform**

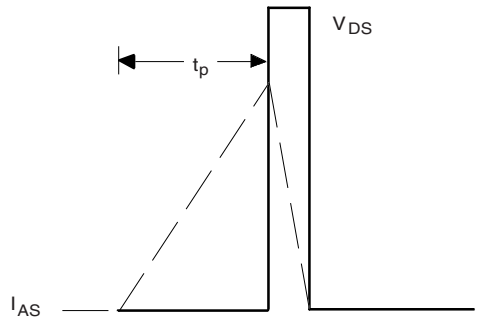



**Fig. 13b - Unclamped Inductive Waveforms**

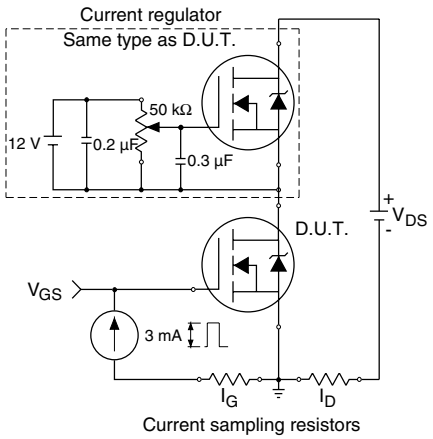
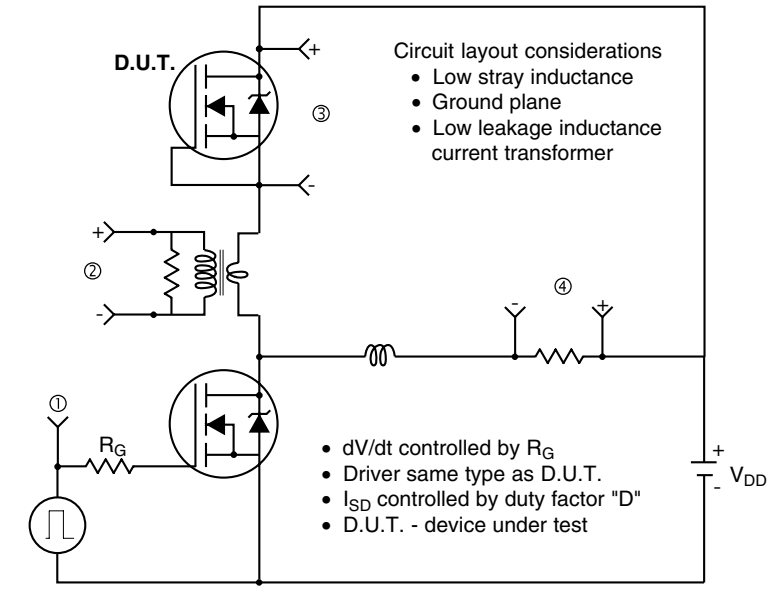
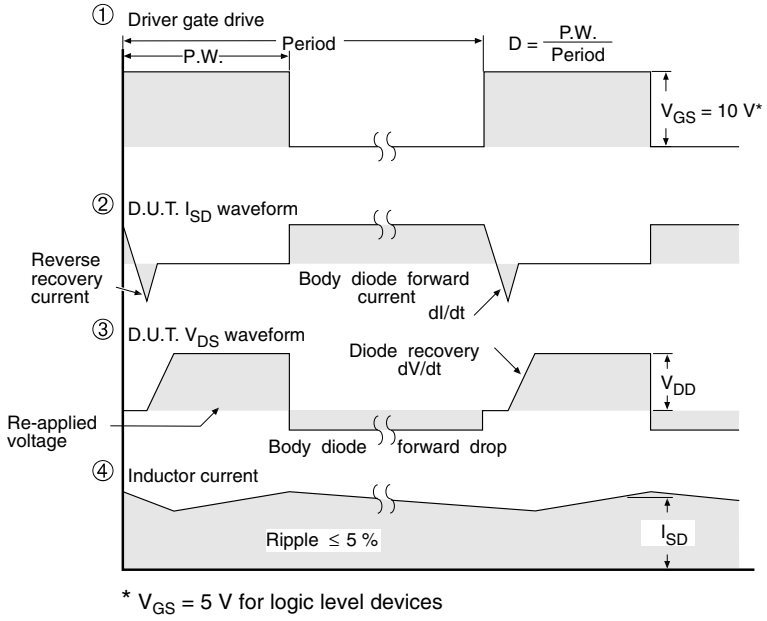



**Fig. 14b - Gate Charge Test Circuit**

## Peak Diode Recovery dV/dt Test Circuit




* $V_{GS}$ = 5 V for logic level devices

**Fig. 15 - For N-Channel**

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